

## Abstract

An electric semiconductor component includes a monocrystalline semiconductor substrate made of silicon, for example, an  
5 insulation layer (6) arranged on the surface of the semiconductor substrate (1) and penetrated by a contact hole (30) in at least one location and a contact element which contacts the semiconductor substrate (1) through the contact hole (30) and is made of a material in which the semiconductor  
10 material of the substrate is soluble in an anisotropic dissolving process. The edges of the contact hole (30) are designed as diffusion stop structures.